

Description

The SX80N08NF uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.

General Features

$V_{DS} = 80V$ $I_D = 80A$

$R_{DS(ON)} < 5.5m\Omega$ $V_{GS}=10V$

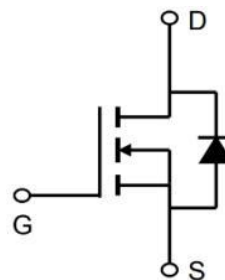
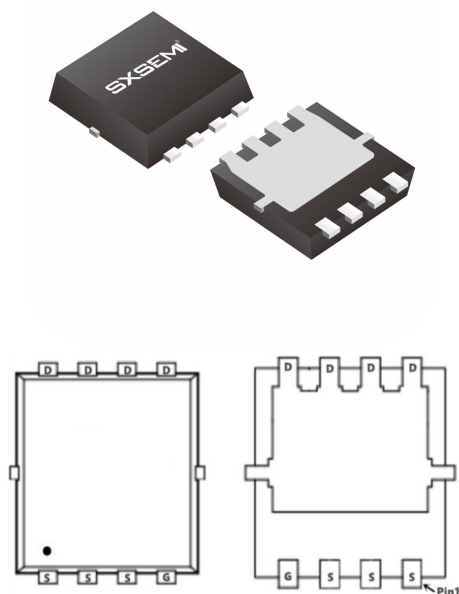
Application

Battery protection

Load switch

Uninterruptible power supply

PDFN5*6-8L



Absolute Maximum Ratings ($T_c=25^\circ C$ unless otherwise noted)

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	80	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D @ T_c=25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^{1,6}$	80	A
$I_D @ T_c=100^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^{1,6}$	42.5	A
I_{DM}	Pulsed Drain Current ²	170	A
E_{AS}	Single Pulse Avalanche Energy ³	57.8	mJ
I_{AS}	Avalanche Current	34	A
$P_D @ T_c=25^\circ C$	Total Power Dissipation ⁴	56	W
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ C$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ C$
$R_{\theta JA}$	Thermal Resistance Junction-Ambient ¹	62	$^\circ C/W$
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	2.2	$^\circ C/W$

Electrical Characteristics (T_J=25 °C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V , I _D =250uA	80	88	---	V
R _{DS(ON)}	Static Drain-Source On-Resistance ²	V _{GS} =10V , I _D =20A	---	3.9	5.5	mΩ
R _{DS(ON)}	Static Drain-Source On-Resistance ²	V _{GS} =4.5V , I _D =20A	---	5.5	8.5	mΩ
V _{GS(th)}	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =250uA	1.2	1.9	2.5	V
I _{DSS}	Drain-Source Leakage Current	V _{DS} =64V , V _{GS} =0V , T _J =25°C	---	---	1	uA
		V _{DS} =64V , V _{GS} =0V , T _J =55°C	---	---	5	
I _{GSS}	Gate-Source Leakage Current	V _{GS} =±20V , V _{DS} =0V	---	---	±100	nA
g _{fs}	Forward Transconductance	V _{DS} =5V , I _D =20A	---	75	---	S
R _g	Gate Resistance	V _{DS} =0V , V _{GS} =0V , f=1MHz	---	0.5	---	Ω
Q _g	Total Gate Charge (10V)	V _{DS} =40V , V _{GS} =10V , I _D =20A	---	40	---	nC
Q _{gs}	Gate-Source Charge		---	7.2	---	
Q _{gd}	Gate-Drain Charge		---	6.5	---	
T _{d(on)}	Turn-On Delay Time	V _{DD} =40V , V _{GS} =10V , R _G =3Ω , I _D =20A	---	8.3	---	ns
T _r	Rise Time		---	4.2	---	
T _{d(off)}	Turn-Off Delay Time		---	36	---	
T _f	Fall Time		---	6.9	---	
C _{iss}	Input Capacitance	V _{DS} =40V , V _{GS} =0V , f=1MHz	---	2860	---	pF
C _{oss}	Output Capacitance		---	410	---	
C _{rss}	Reverse Transfer Capacitance		---	38	---	
I _S	Continuous Source Current ^{1,5}	V _G =V _D =0V , Force Current	---	---	48	A
V _{SD}	Diode Forward Voltage ²	V _{GS} =0V , I _S =A , T _J =25°C	---	0.77	1.0	V
t _{rr}	Reverse Recovery Time	I _F =20A , di/dt=100A/μs , T _J =25°C	---	27	---	nS
Q _{rr}	Reverse Recovery Charge		---	89	---	nC

Note :

1.The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.

2.The data tested by pulsed , pulse width ≤ 300us , duty cycle ≤ 2%

3.The EAS data shows Max. rating . The test condition is V_{DD}=25V,V_{GS}=10V,L=0.1mH,I_{AS}=34A

4.The power dissipation is limited by 150°C junction temperature

5.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.

6.The maximum current rating is package limited.

Typical Characteristics

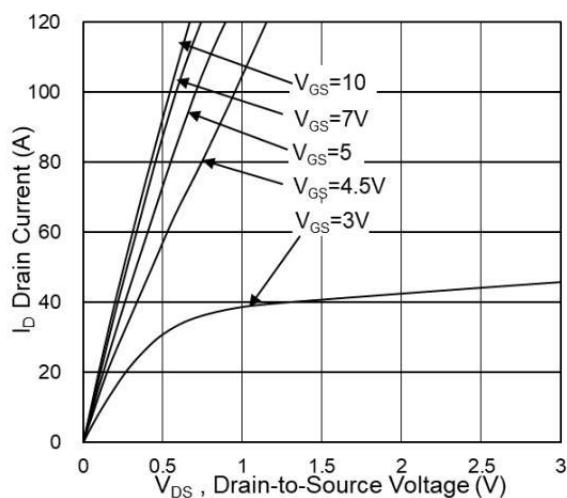


Fig.1 Typical Output Characteristics

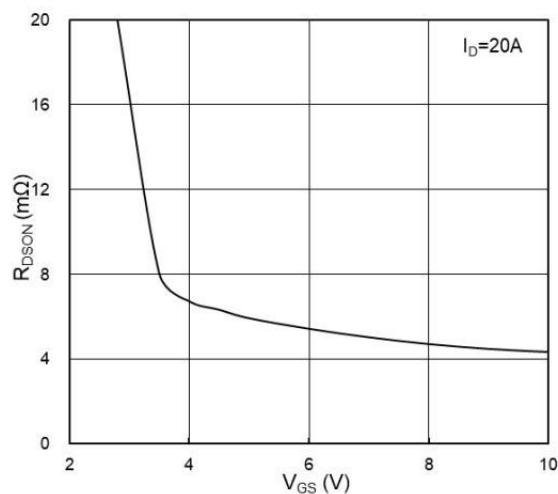


Fig.2 On-Resistance vs G-S Voltage

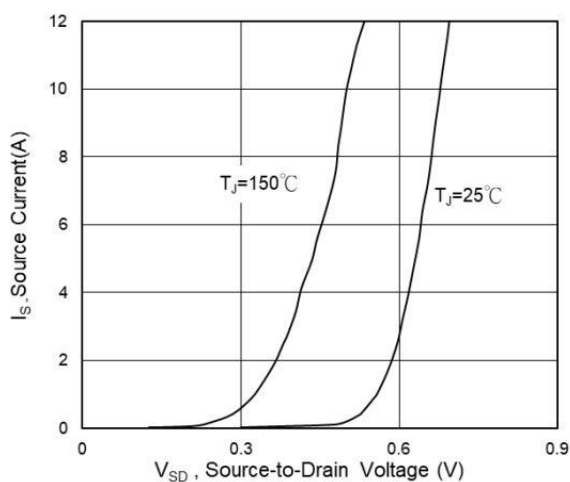


Fig.3 Source Drain Forward Characteristics

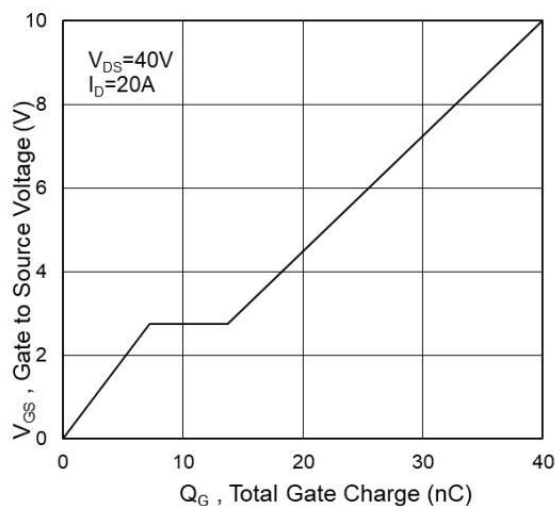


Fig.4 Gate-Charge Characteristics

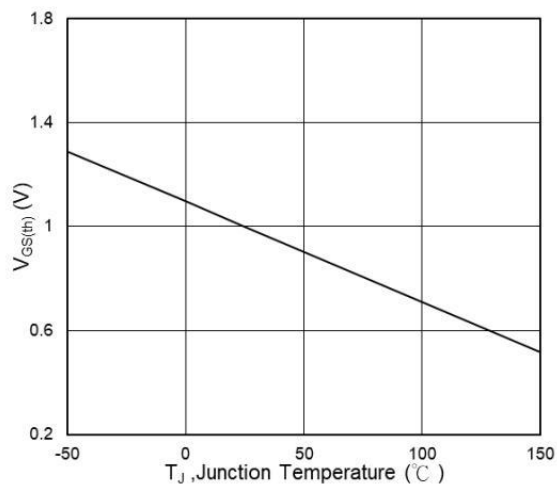


Fig.5 Normalized $V_{GS(th)}$ vs. T_J

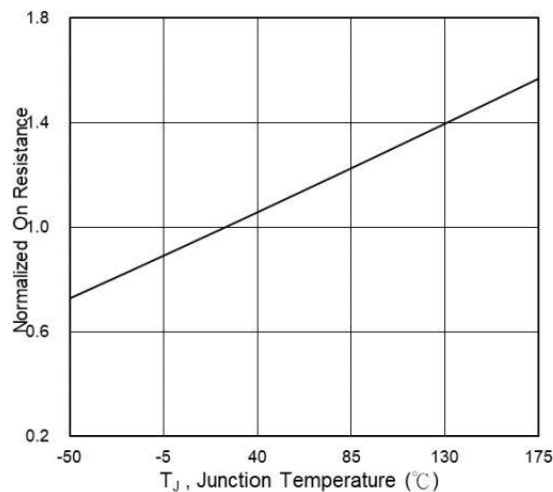


Fig.6 Normalized $R_{DS(on)}$ vs. T_J

Typical Characteristics

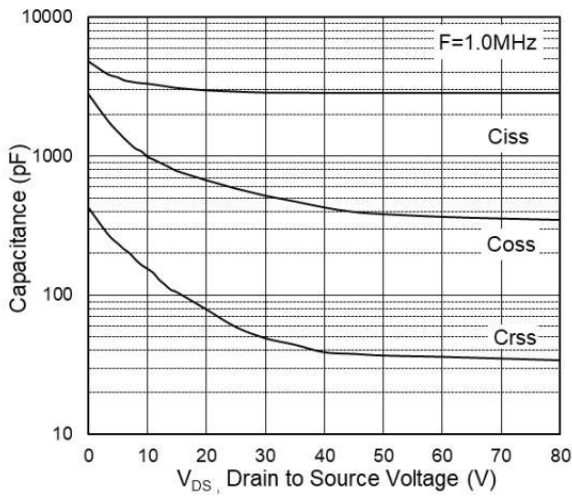


Fig.7 Capacitance

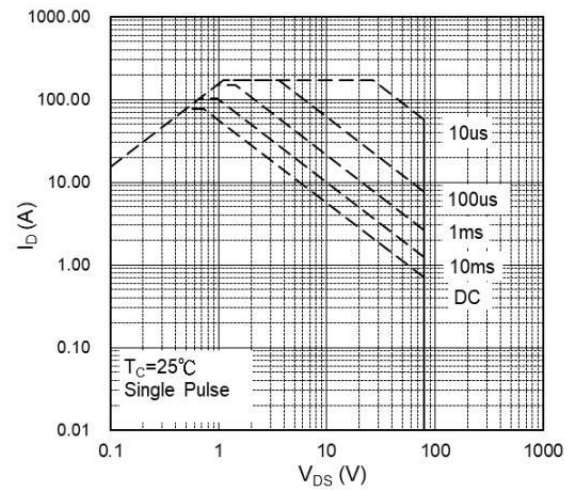


Fig.8 Safe Operating Area

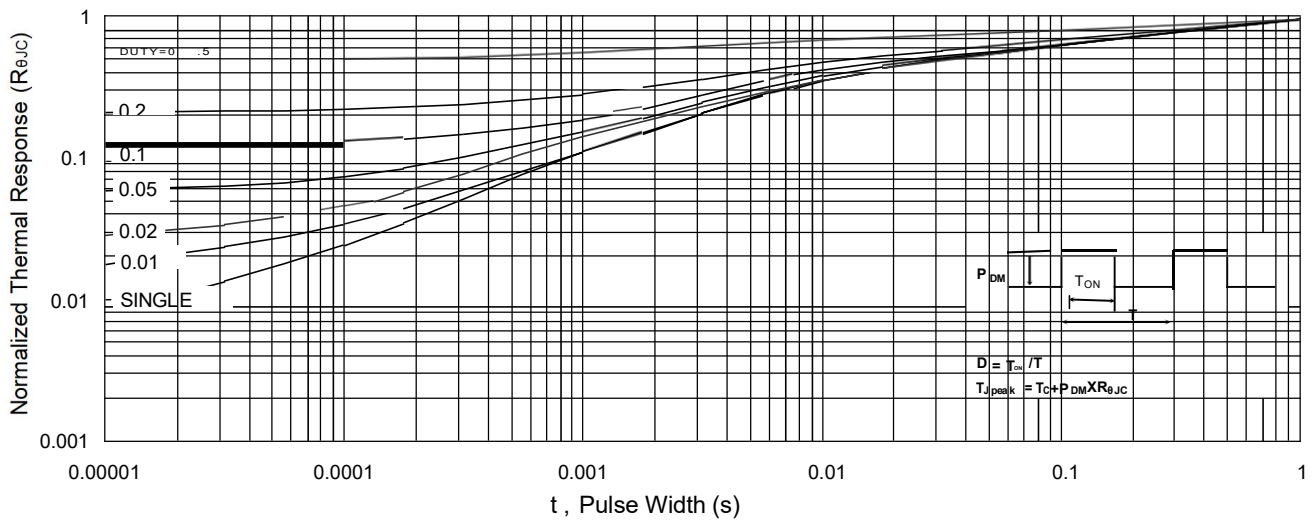


Fig.9 Normalized Maximum Transient Thermal Impedance

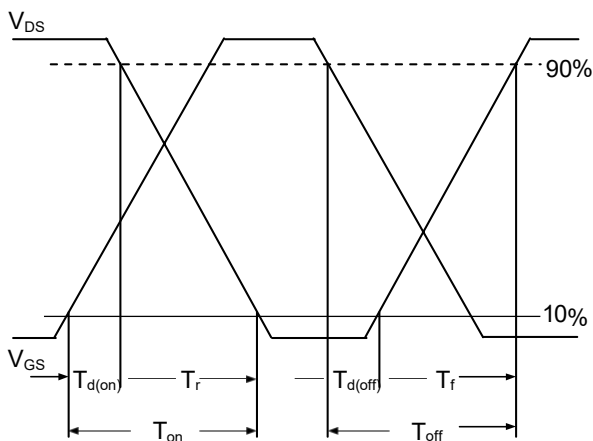


Fig.10 Switching Time Waveform

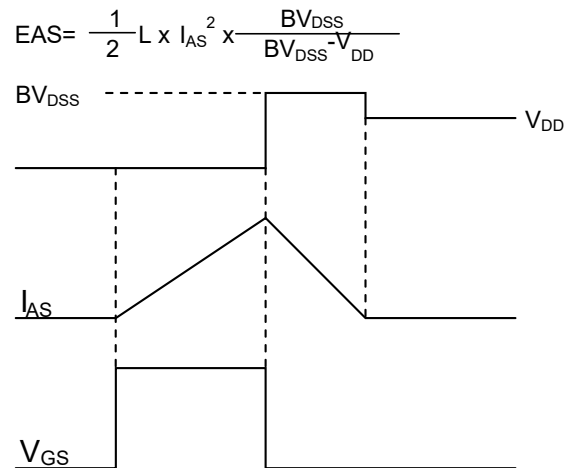
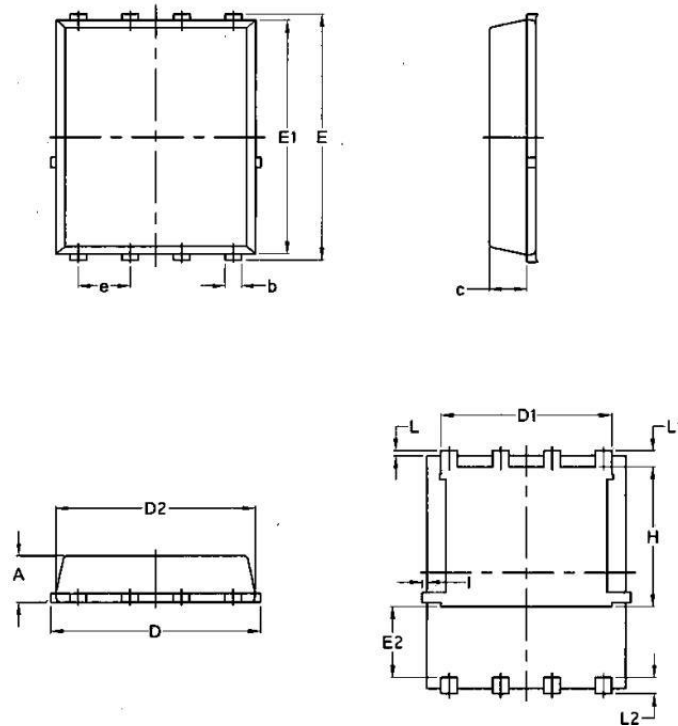


Fig.11 Unclamped Inductive Switching Waveform

MOSFET Package Mechanical Data- PDFN5*6-8L-JQ Single



Symbol	Common			
	mm		Inch	
	Mim	Max	Min	Max
A	1.03	1.17	0.0406	0.0461
b	0.34	0.48	0.0134	0.0189
c	0.824	0.0970	0.0324	0.082
D	4.80	5.40	0.1890	0.2126
D1	4.11	4.31	0.1618	0.1697
D2	4.80	5.00	0.1890	0.1969
E	5.95	6.15	0.2343	0.2421
E1	5.65	5.85	0.2224	0.2303
E2	1.60	/	0.0630	/
e	1.27 BSC		0.05 BSC	
L	0.05	0.25	0.0020	0.0098
L1	0.38	0.50	0.0150	0.0197
L2	0.38	0.50	0.0150	0.0197
H	3.30	3.50	0.1299	0.1378
I	/	0.18	/	0.0070

Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
TAPING	PDFN5*6-8L		5000